5 é / Descriptions

SOP-8 .> / / x ; m Í % ” MOS « | • ’ož

Complementary Enhancement MOSFET in a SOP-8 Plastic Package.

¤ ª / Features

N-channel	P-channel
V_{DS}(V)=30V	V_{DS}(V)=-30V
I_D=7.2A	I_D=-7A
$R_{DS(ON)}$<25m ¡ (V_{GS}=10V)	$R_{DS(ON)}$<25m ¡ (V_{GS}=-10V)
$R_{DS(ON)}$<35m ¡ (V_{GS}=4.5V)	$R_{DS(ON)}$<35m ¡ (V_{GS}=-4.5V)

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Ð ÷ / Applications

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These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies. And suitable for use as a load switch or in PWM applications.

Ã W] Ô · / Equivalent Circuit

• Û - æ / Pinning

PIN1 y S1 PIN 2 y G1 PIN 3 y S2 PIN 4 y G2

PIN 5 y D2 PIN 6 y D2 PIN 7 y D1 PIN 8 y D1

, M V / Marking

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See Marking Instructions.

Ã a ? d / Absolute Maximum Ratings(Ta=25 ;)

@ ƒ Parameter	… Z Symbol		ƒ › Rating		% y Unit
			N-channel	P-channel	
Drain-Source Voltage	V_{DSS}		±30		V
Gate-Source Voltage	V_{GSS}		±20		V
Continuous Drain Current	I_D (T_A=25)		7.2	-7	A
Pulsed Drain Current	I_{DM}		±40		A
Power Dissipation	P_D (T_A=25)		2		W
Maximum Junction-to-Ambient	R_{JA}	t ”10s	62.5		/W
		Steady-State	90		/W
Maximum Junction-to-Lead	R_{JL}	Steady-State	40		/W
Junction and Storage Temperature Range	T_J,T_{STG}		-55 to +150		

@ *f* Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250 A	30	32		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V V_{GS}=0V			1.0	A
Gate-Body leakage current	I_{GSS}	V_{GS}=±20V V_{DS}=0V			100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250 A	1.0	1.7	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V I_D=7.2A		21	25	m

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1 ?è Ô ? d • Ž ¢ / N-CHANNEL Electrical Characteristic Curve

@ *f* Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250 A	-30	-33		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V V_{GS}=0V			-1.0	A
Gate-Body leakage current	I_{GSS}	V_{GS}=±20V V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=-250 A	-1.0	-1.5	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$					

3 ?è Ô ? d • Ž ¢ / P-CHANNEL Electrical Characteristic Curve

3 ?è Ô ? d • Ž ¢ / P-CHANNEL Electrical Characteristic Curve

Ø ¤ =) ¢ / Package Dimensions

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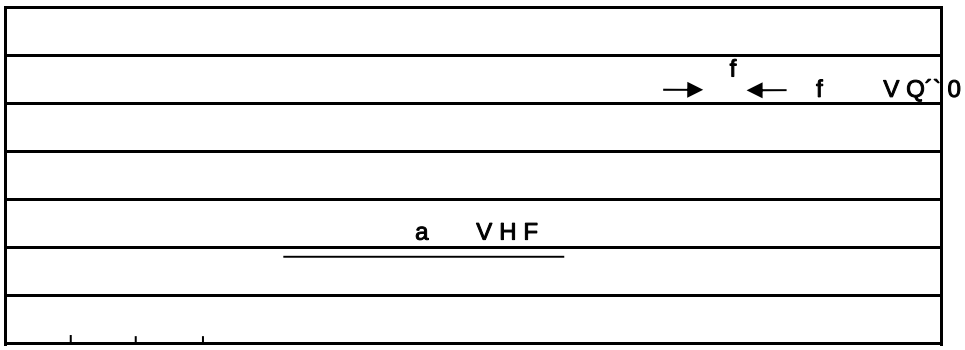
š WD t … • Ž ¢ (x /) / : K S V K X G Z [X K 6 X U L O R K L U X / 8 8 K L R U] 9 U R J K X O T M 6



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1o• Ä ½ “ † 150 ½180 - k ž • 60 ½90sec;

2o• Q › “ † 245 r5 - k ž • 4 Ò 5 r0.5sec;

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

Note:

1.Preheating:150~180 - , Time:60~90sec.

2.Peak Temp.:245 r5 - , Duration:5 r0.5sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ¯ »] / Resistance to Soldering Heat Test Conditions

“ † y 260 r5 - ž • y 10 r1 sec. Temp.:260±5 Time:10±1 sec

G P á / Packaging SPEC.

2 & x / REEL

Package Type 7>û ˜ E	Units ;>û ¦H					Dimension ;>û p . (unit Æmm³)		
	Units/Reel / --	Reels/Inner Box -- /-	Units/Inner Box /-	Inner Boxes/Outer Box - /1ç	Units/Outer Box /1ç	Reel	Inner Box×	Outer Box1ç ¦